

# **PSMN005-30K**

# N-channel TrenchMOS SiliconMAX logic level FET

Rev. 2 — 22 December 2011

**Product data sheet** 

## 1. Product profile

### 1.1 General description

SiliconMAX logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- Computer motherboards
- DC-to-DC convertors

Switched-mode power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	30	V				
I <sub>D</sub>	drain current	$T_{sp} = 80  ^{\circ}C; V_{GS} = 10  V; see \frac{Figure  1}{}$	-	-	20	Α				
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 80 °C; see <u>Figure 2</u>	-	-	3.5	W				
Static characte	Static characteristics									
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	4.4	5.5	mΩ				
Dynamic char	Dynamic characteristics									
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 20 \text{ A}; V_{DS} = 15 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{ Implies to the content of the conten$	-	14	-	nC				



# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	8 <u>7 7 7 7</u> 5	D
3	S	source		<sub>G</sub> (巨本)
4	G	gate		
5	D	drain	1	mbb076 S
6	D	drain	SOT96-1 (SO8)	
7	D	drain		
8	D	drain		

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN005-30K	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	30	V
$V_{GS}$	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$T_{sp} = 80  ^{\circ}C; V_{GS} = 10  V; see  \underline{Figure  1}$	-	20	Α
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see <u>Figure 3</u>	-	60	Α
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 80 °C; see <u>Figure 2</u>	-	3.5	W
T <sub>stg</sub>	storage temperature		-55	150	°C
T <sub>j</sub>	junction temperature		-55	150	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>sp</sub> = 80 °C	-	20	Α
I <sub>SM</sub>	peak source current	$T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \mu s$	-	60	Α

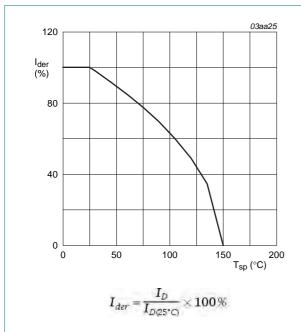


Fig 1. Normalized continuous drain current as a function of solder point temperature

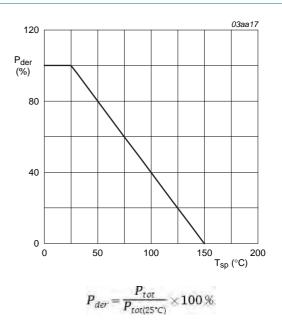
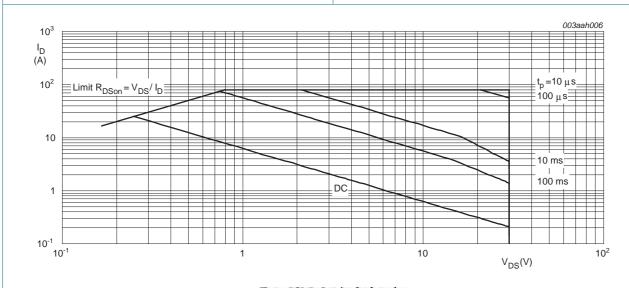


Fig 2. Normalized total power dissipation as a function of solder point temperature



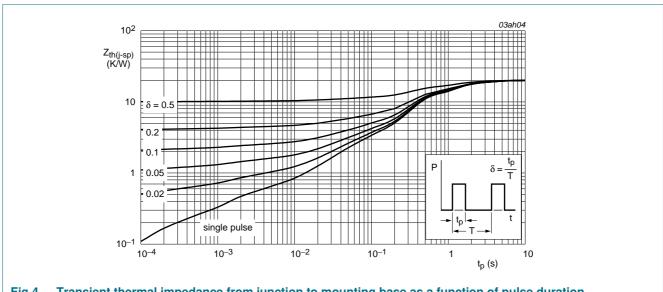
 $T_{SP} = 25^{\circ}C$ ;  $I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

# Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	mounted on a metal clad board; see Figure 4	-	-	20	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 150 \text{ °C}$ ; see Figure 8	0.5	-	-	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 8	-	-	3.4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 8	1	-	3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	0.5	mA
I <sub>GSS</sub> gate leaka	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}$ ; $I_D = 13 \text{ A}$ ; $T_j = 25 \text{ °C}$ ; see Figure 9; see Figure 10	-	6.6	8	mΩ	
		$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	4.4	5.5	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 20 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	34	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 11</u>	-	15	-	nC
$Q_{GD}$	gate-drain charge		-	14	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	3100	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 12</u>	-	605	-	pF
$C_{rss}$	reverse transfer capacitance		-	405	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 15 \Omega; V_{GS} = 10 \text{ V};$	-	18	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	16	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	65	-	ns
t <sub>f</sub>	fall time		-	45	-	ns
9 <sub>fs</sub>	transfer conductance	$V_{DS} = 15 \text{ V}; I_D = 20 \text{ A}; T_j = 25 \text{ °C}$	-	60	-	S
Source-di	rain diode					
$V_{SD}$	source-drain voltage	$I_S$ = 15 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 13</u>	-	0.81	1.3	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	35	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	20	-	nC

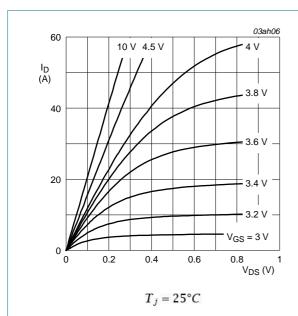


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

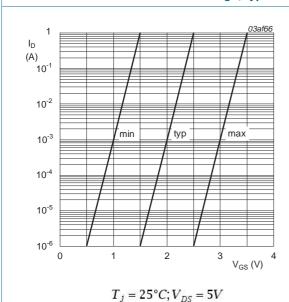


Fig 7. Sub-threshold drain current as a function of gate-source voltage

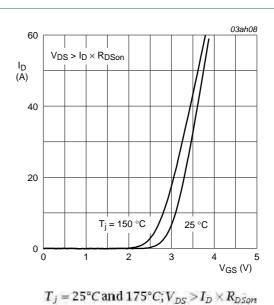


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

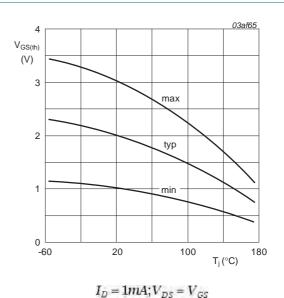


Fig 8. Gate-source threshold voltage as a function of junction temperature

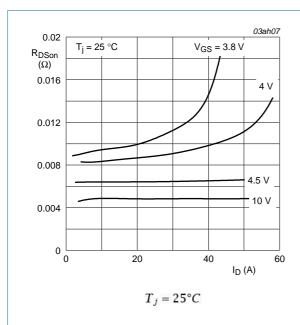


Fig 9. Drain-source on-state resistance as a function of drain current; typical values

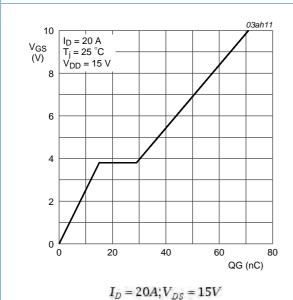


Fig 11. Gate-source voltage as a function of gate charge; typical values

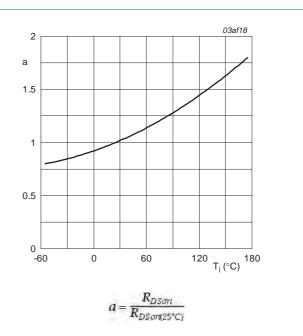


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

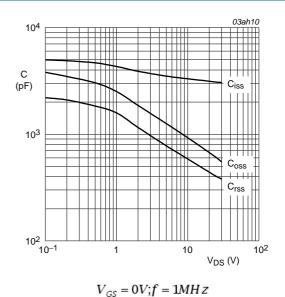


Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

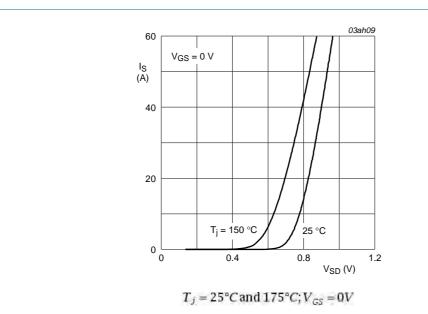
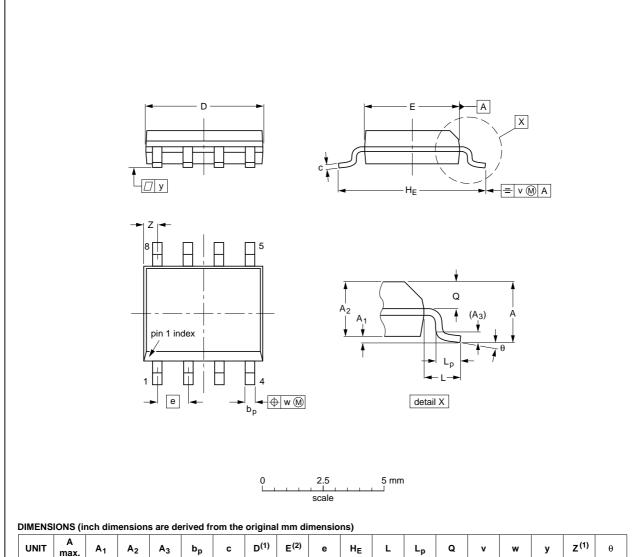


Fig 13. Source current as a function of source-drain voltage; typical values

# 7. Package outline

### SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



	,																	
UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Ø	v	w	у	Z <sup>(1)</sup>	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012				<del>99-12-27</del> 03-02-18

Fig 14. Package outline SOT96-1 (SO8)

PSMN005-30K

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# N-channel TrenchMOS SiliconMAX logic level FET

# 8. Revision history

#### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN005-30K v.2	20111222	Product data sheet	-	PSMN005-30K_1
Modifications:	<ul> <li>Various chang</li> </ul>			
PSMN005-30K_1	20091117	Product data sheet	-	-

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#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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